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Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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RF & MICROWAVE TRANSISTORS L-BAND RADAR APPLICATIONS

Features

- 1090 MHz
- 50 VOLTS
- **P**_{OUT} = 75 WATTS
- $G_P = 9.2 \text{ dB MINMUM}$
- 10:1 VSWR CAPABILITY
- COMMON BASE CONFIGURATION

DESCRIPTION:

The MS2228 device is a high power Class C transistor specifically designed for L-Band Avionics transponder/interrogator pulsed output and driver applications.

This device is capable of operation over a wide range of pulse widths, duty cycles, and is capable of withstanding 10:1 output VSWR at rated RF conditions. Internal input and output matching provide optimum performance and product consistency.

.400 x .400 2LFL M214 hermetically sealed



ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
PDISS	Power Dissipation	175	W
Ι _C	Device Current	5.4	Α
Vcc	Collector-Supply Voltage	55	V
TJ	Junction Temperature	200	°C
T _{STG}	Storage Temperature	-65 to +200	°C

Thermal Data

R _{TH(J-C)}	Thermal Resistance Junction-case*	0.86	°C/W
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Revision A, October 2009



ELECTRICAL SPECIFICATIONS (Tcase = 25° C)

STATIC

Symbol	Test Conditions		Value			
Symbol	Symbol Test Conditions		Min.	Тур.	Max.	Onit
BV _{CBO}	l _c = 10 mA	l _E = 0 mA	65			V
BV _{EBO}	I _E = 4 mA	$I_c = 0 mA$	3.5			V
BV _{CER}	l _c = 20 mA	R _{BE} = 10Ω	65			V
I _{CES}	V _{CE} = 50 V				6	mA
HFE	$V_{CE} = 5 V$	$I_{\rm C} = 1 {\rm A}$	10			

DYNAMIC

			Value				
Symbol	Test Conditions		Min.	Тур.	Max.	Unit	
Ρουτ	f = 1090 MHz	P _{IN} = 9W	$V_{\rm CC} = 50V$	75			W
G _P	f = 1090 MHz	P _{IN} = 9W	$V_{\rm CC} = 50V$	9.2			dB
η _c	f = 1090 MHz	P _{IN} = 9W	$V_{\rm CC} = 50V$	48			%

Conditions: Pulse Width = $32 \mu sec$ Duty Cycle = 2%



IMPEDANCE DATA

FREQ	$Z_{IN}(\Omega)$	$Z_{cc}(\Omega)$		
1030 MHz	7.0 + j3.0	12.5 - j4.5		
1090 MHz	11.0 + j1.5	13.0 - j3.0		

 $P_{IN} = 9.0W$

 $V_{CC} = 50V$

TEST CIRCUIT



All dimensions are in inches. Substrate material: .025 thick Al₂O₃

- : 0.8-8.0 pF Johanson Gigatrim Capacitor C1
- 100 pF Chip Capacitor C2 :
- : 1500 pF Filtercon Feedthru C3



- C4 : 1 µF, Ceramic Capacitor

- C5 : 100 μF, Electrolytic Capacitor RFC 1: Au Plated Ni Strap 0.280 Long x 0.035 Wide x 0.005 Thick
- RFC 2: #26 Wire, 4 Turn 1/16 I.D.



TYPICAL PERFORMANCE



Microsemi reserves the right to change, without notice, the specifications and information contained herein. Visit our web site at <u>www.microsemi.com</u> or contact our factory direct.



PACKAGE MECHANICAL DATA

